TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1203

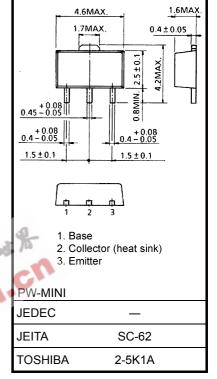
Audio Frequency Amplifier Applications

Unit: mm

- Suitable for output stage of 3 watts amplifier
- · Small flat package
- $\bullet~$ $P_{\rm C}$ = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SC2883

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	-30	V	
Collector-emitter voltage	V _{CEO}	-30	٧	
Emitter-base voltage	V _{EBO}	-5	V	
Collector current	IC	-1.5	Α	
Base current	ΙΒ	-0.3	Α	
Collector power dissipation	PC	500	、落	
	PC	1000	mW	
	(Note 1)	1000	-0	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	



Weight: 0.05 g (typ.)

Note 1: Mounted on a ceramic substrate (250 mm² × 0.8 t)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

temperature/current/voltage, etc.) are within the absolute maximum ratings.

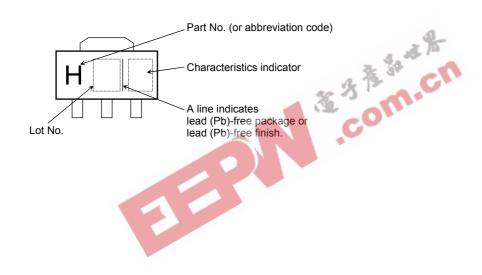
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

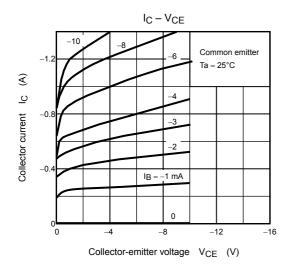
Electrical Characteristics (Ta = 25°C)

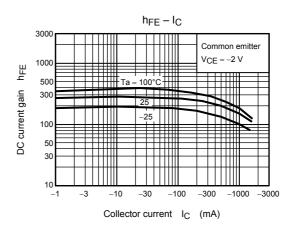
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -30 \text{ V}, I_{E} = 0$	_	_	-0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V, I _C = 0	_	_	-0.1	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	I _C = -10 mA, I _B = 0	-30	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_E = -1 \text{ mA}, I_C = 0$	-5	_	_	V
DC current gain	h _{FE} (Note 3)	V _{CE} = -2 V, I _C = -500 mA	100	_	320	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = -1.5 A, I _B = -0.03 A	_	_	-2.0	V
Base-emitter voltage	V _{BE}	V _{CE} = -2 V, I _C = -500 mA	_	_	-1.0	V
Transition frequency	f _T	V _{CE} = -2 V, I _C = -500 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	_	50	pF

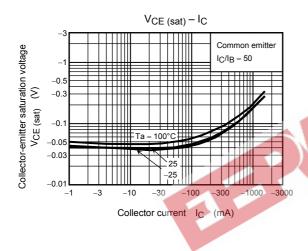
Note 3: hFE classification O: 100 to 200, Y: 160 to 320

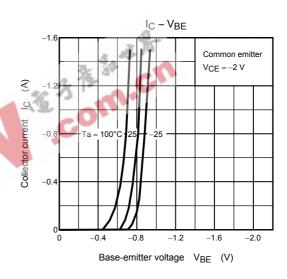
Marking

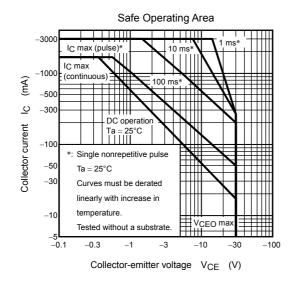


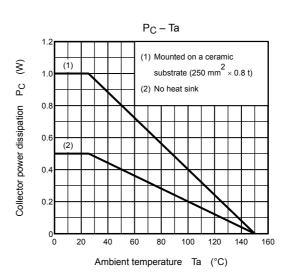












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